

## FEATURES

Complementary Type The NPN Transistor  
MMBT3904 is Recommended  
Epitaxial Planar Die Construction



## MARKING: 2A

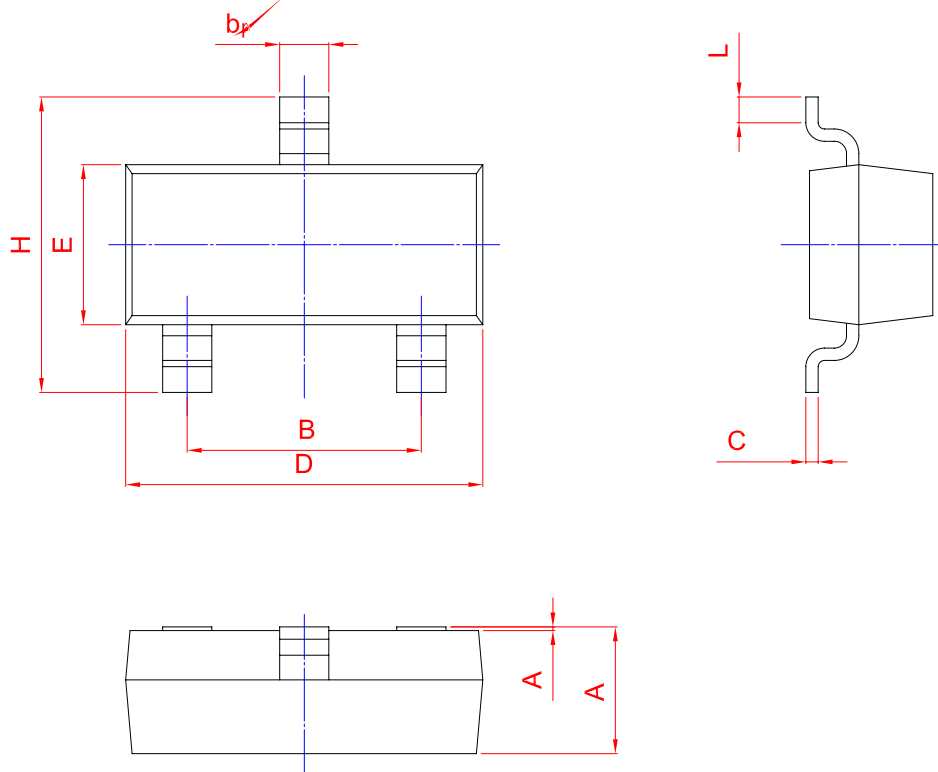
## MAXIMUM RATINGS ( $T_a=25$ unless otherwise noted)

| Symbol    | Parameter                              | Value      | Unit |
|-----------|----------------------------------------|------------|------|
| $V_{CBO}$ | Collector-Base Voltage                 | -40        | V    |
| $V_{CEO}$ | Collector-Emitter Voltage              | -40        | V    |
| $V_{EBO}$ | Emitter-Base Voltage                   | -5         | V    |
| $I_C$     | Collector Current                      | -200       | mA   |
| $P_C$     | Total Device Dissipation               | 200        | mW   |
| $R_{JA}$  | Thermal Resistance Junction to Ambient | 625        | /W   |
| $T_J$     | Junction Temperature                   | 150        |      |
| $T_{stg}$ | Storage Temperature                    | -55 ~ +150 |      |

## ELECTRICAL CHARACTERISTICS ( $T_a=25$ unless otherwise specified)

| Parameter                        | Symbol        | Test conditions       | Min | Max | Unit |
|----------------------------------|---------------|-----------------------|-----|-----|------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C=-10\mu A, I_E=0$ | -40 |     | V    |





| UNIT | A    |  | $b_p$ | C    | D    | E    | H <sub>h</sub> | A <sub>1</sub> | L <sub>p</sub> |
|------|------|--|-------|------|------|------|----------------|----------------|----------------|
| mm   | 1.40 |  | 0.50  | 0.19 | 3.10 | 1.65 | 3.00           | 0.100          | 0.50           |
|      | 0.95 |  | 0.35  | 0.08 | 2.70 | 1.20 | 2.20           | 0.013          | 0.20           |